

系組：電機系丙組、電機系海外、光電系、生醫所

准考證號碼：□□□□□□□□

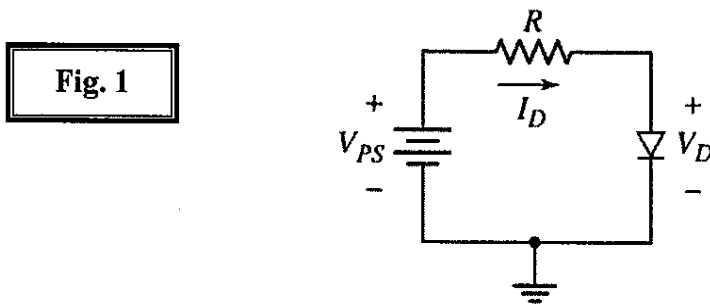
科目：電子學(145)

(請考生自行填寫)

注意事項	一、請先檢查准考證號碼、報考系(組)別、考試科目名稱，確定無誤後再作答。 二、所有答案應寫於答案紙上，否則不予計分。 三、作答時應依試題題號，依序由上而下書寫，作答及未作答之題號均應抄寫。
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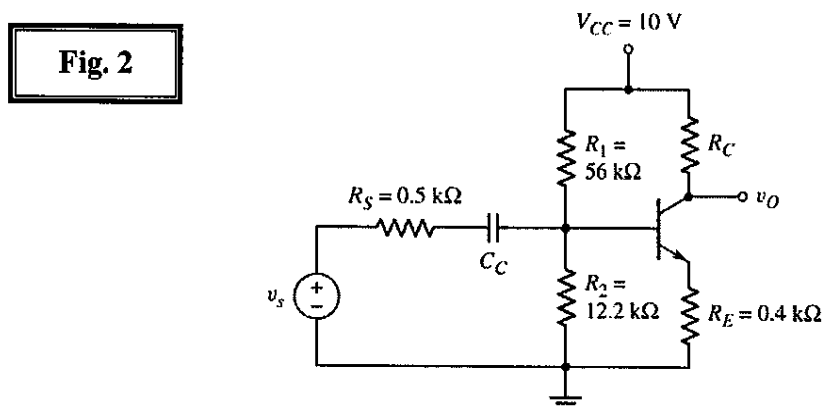
1. For the circuit in Fig. 1, assume that the diode has the cut-in voltage of $V_f = 0.6 \text{ V}$ and the forward resistance of $r_f = 10 \Omega$.

- (1) If $V_{PS} = 2 \text{ V}$ and $R = 2 \text{ k}\Omega$, determine the diode voltage V_D . (5%)
- (2) If $V_{PS} = 5 \text{ V}$ and $R = 2 \text{ k}\Omega$ and the diode forward resistance r_f is changed to be 0Ω , plot the diode I-V characteristics and the load line to find the Q-point (V_D and I_D). (5%)
- (3) If $V_{PS} = 0.2 \text{ V}$ and $R = 2 \text{ k}\Omega$, determine the diode current I_D . (5%)



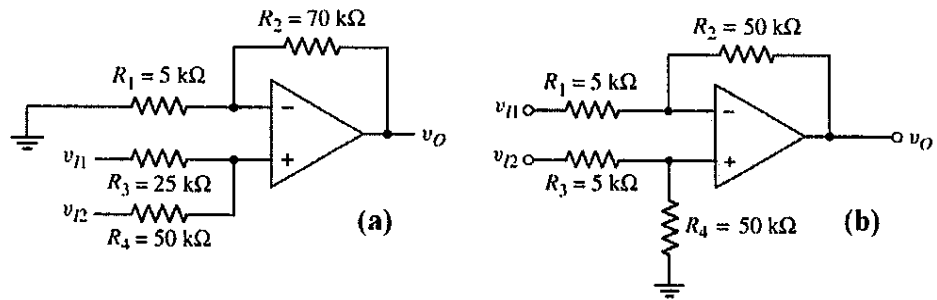
2. For the circuit in Fig. 2, the transistor parameters are: $V_{BE(ON)} = 0.7 \text{ V}$, $\beta = 100$, and $V_A = \infty$.

- (1) If $I_{CQ} = 2.16 \text{ mA}$ and $V_{CEQ} = 4.81 \text{ V}$, determine the value of R_C . (5%)
- (2) Plot the small-signal equivalent circuit of the circuit. (5%)
- (3) Determine the input resistance looking into the base of the transistor. (5%)
- (4) Determine the small-signal approximate voltage gain $A_v \cong v_o / v_s$. (5%)

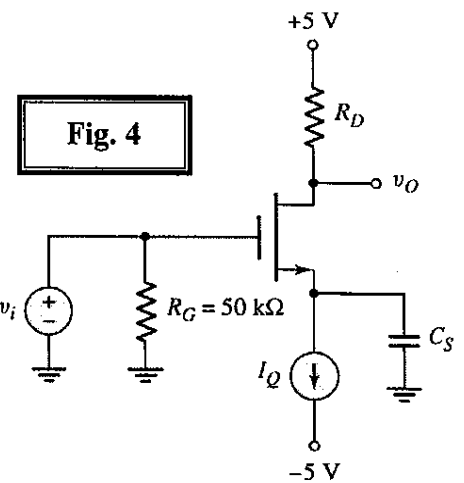


3. In **Fig. 3**, assume the op amps are ideal and let $v_{I1} = 1\text{ V}$ and $v_{I2} = 2\text{ V}$.
- (1) Determine the output voltage v_o in **Fig. 3 (a)**. (5%)
 - (2) Determine the output voltage v_o in **Fig. 3 (b)**. (5%)
 - (3) In **Fig. 3 (b)**, if R_4 is changed to be $55\text{ k}\Omega$, determine the CMRR (dB). (10%)

Fig. 3

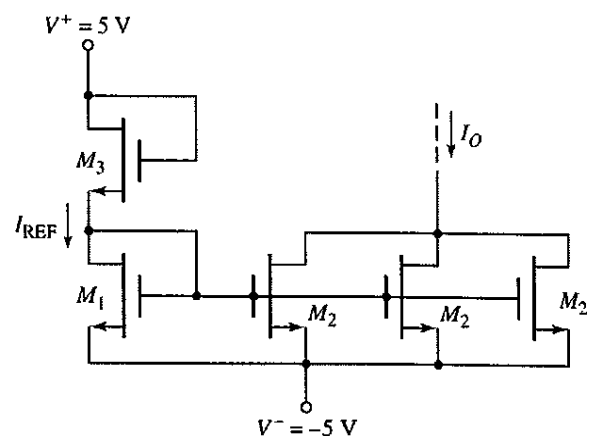


4. The circuit in **Fig. 4** has $R_D = 4\text{ k}\Omega$, $I_Q = 0.5\text{ mA}$ and transistor parameters $V_{TN} = 1.5\text{ V}$, $\mu_n C_{ox} = 40\mu\text{A}/\text{V}^2$, and $\lambda = 0$. If the small-signal voltage gain is $A_v = v_o / v_i = -4$,
- (1) Find the transconductance g_m of the transistor. (5%)
 - (2) Determine the width-to-length ratio W/L of the transistor. (5%)
 - (3) Calculate V_{GSQ} and V_{DSQ} . (10%)



5. Consider the circuit shown in **Fig. 5**. The transistor parameters are:
 $V_{TN} = 2\text{ V}$, $K_{n1} = K_{n2} = 0.4\text{ mA}/\text{V}^2$, $K_{n3} = 0.1\text{ mA}/\text{V}^2$ and $\lambda = 0$.
 All transistors labeled M_2 are identical.
 Determine I_{REF} and I_O . (10%)

Fig. 5



6. Consider the circuit in **Fig. 6**, with transistor parameters: $\beta = 100$, $V_{BE(on)} = 0.7V$, and $V_A = \infty$.

(1) Show
$$I_{C2} = \frac{I_1}{1 + \frac{2}{\beta(1 + \beta)}} \quad (5\%)$$

(2) Find I_{C4} and V_{CE4} . (10%)

Fig. 6

